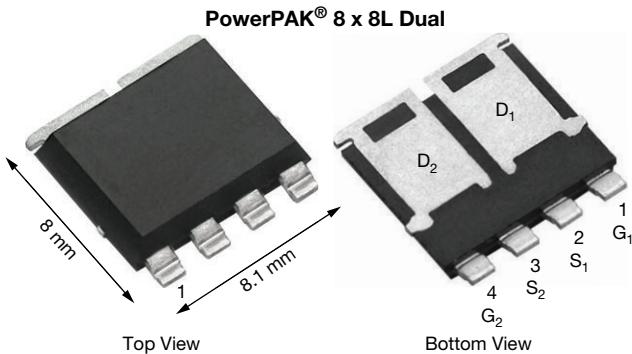


Automotive Dual N-Channel 100 V (D-S) 175 °C MOSFET



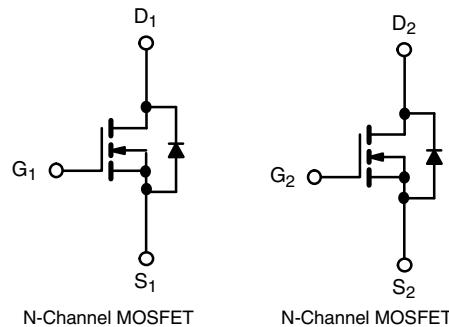
FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R_g and UIS tested
- Fully lead (Pb)-free device
- Material categorization:
for definitions of compliance please see
www.vishay.com/doc/99912



PRODUCT SUMMARY

V_{DS} (V)	100
$R_{DS(on)}$ (Ω) at $V_{GS} = 10$ V	0.0086
$R_{DS(on)}$ (Ω) at $V_{GS} = 4.5$ V	0.0114
I_D (A) per leg	70
Configuration	Dual
Package	PowerPAK 8 x 8L



ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	V_{DS}	100	V
Gate-source voltage	V_{GS}	± 20	
Continuous drain current	$T_C = 25^\circ\text{C}$ ^a	I_D	70
	$T_C = 125^\circ\text{C}$		40
Continuous source current (diode conduction) ^a	I_S	100	A
Pulsed drain current ^b	I_{DM}	280	
Single pulse avalanche current	$L = 0.1\text{ mH}$	I_{AS}	42
Single pulse avalanche energy		E_{AS}	88
Maximum power dissipation ^b	$T_C = 25^\circ\text{C}$	P_D	187
	$T_C = 125^\circ\text{C}$		62
Operating junction and storage temperature range	T_J, T_{stg}	-55 to +175	°C
Soldering recommendations (peak temperature) ^{d, e}		260	

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-ambient	R_{thJA}	85	°C/W
Junction-to-case (drain)	R_{thJC}	2	

Notes

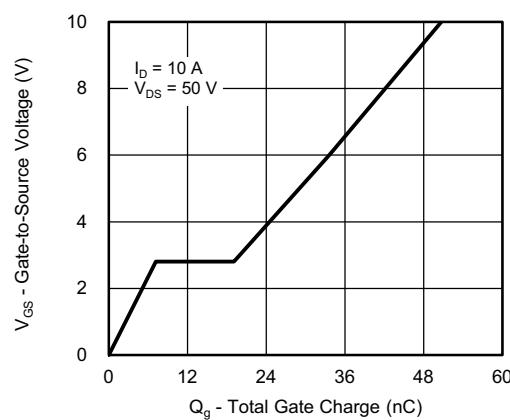
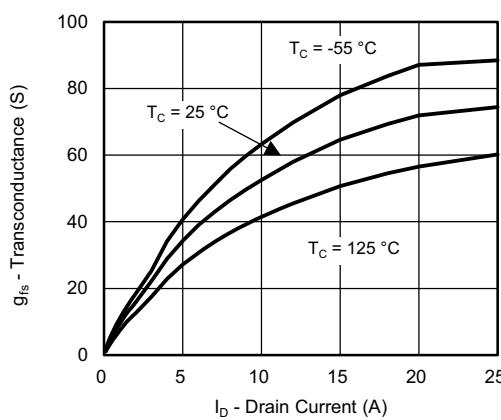
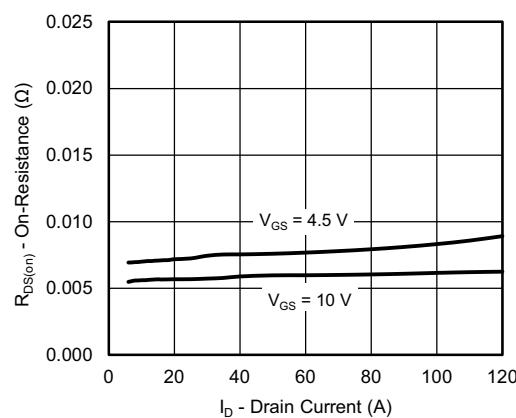
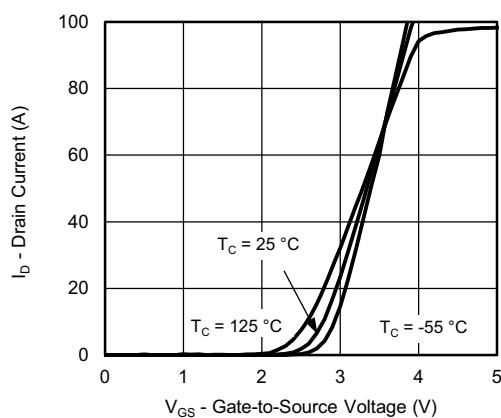
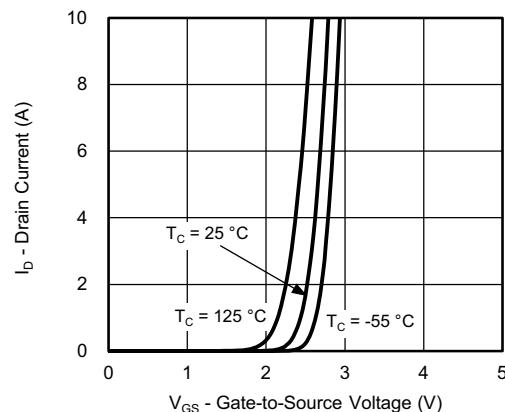
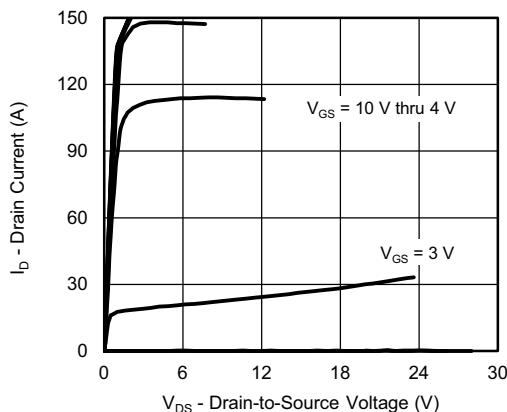
- a. Package limited
- b. Pulse test; pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2 \%$
- c. When mounted on 1" square PCB (FR4 material)
- d. See solder profile (www.vishay.com/doc/73257). The PowerPAK 8 x 8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components

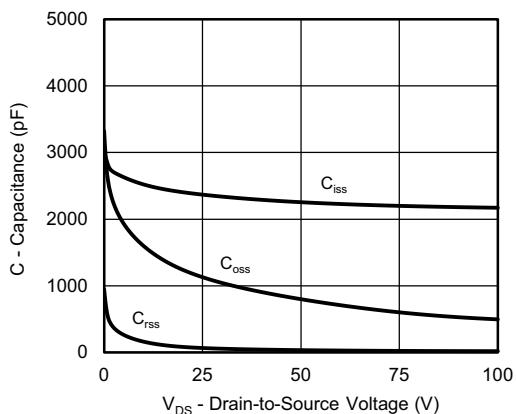
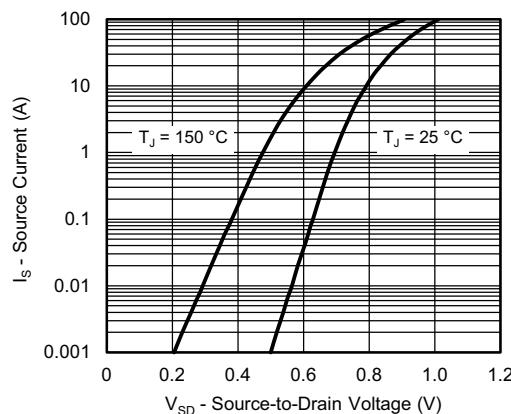
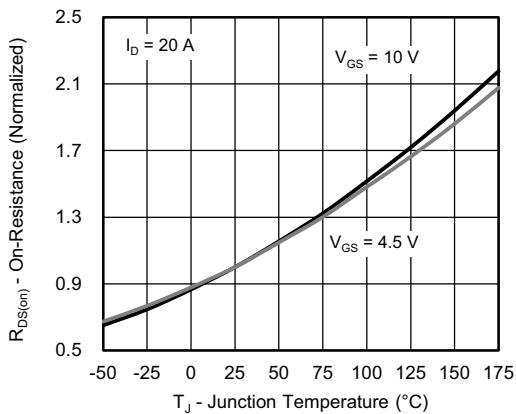
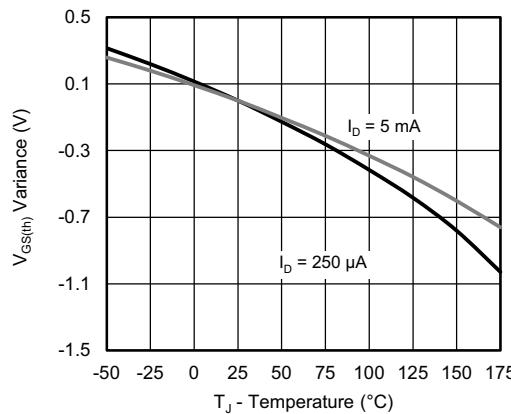
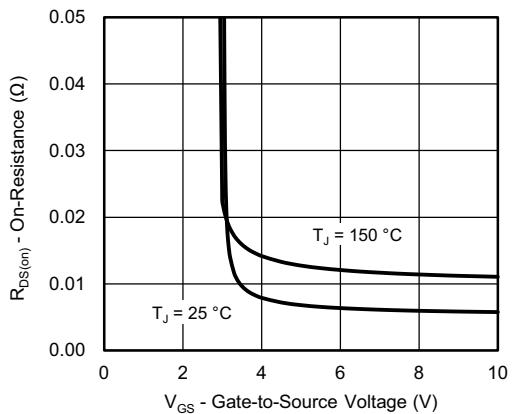
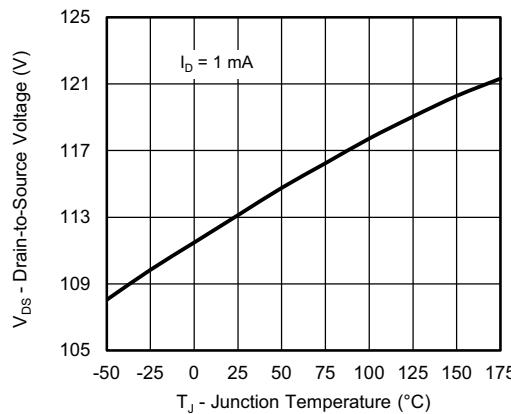
SPECIFICATIONS ($T_C = 25^\circ\text{C}$, unless otherwise noted)								
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static								
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0$, $I_D = 250 \mu\text{A}$		100	-	-	V	
Gate-source threshold voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}$, $I_D = 250 \mu\text{A}$		1.5	2	2.5		
Gate-source leakage	I_{GSS}	$V_{DS} = 0 \text{ V}$, $V_{GS} = \pm 20 \text{ V}$		-	-	± 100	nA	
Zero gate voltage drain current	I_{DSS}	$V_{GS} = 0 \text{ V}$	$V_{DS} = 20 \text{ V}$	-	-	1	μA	
		$V_{GS} = 0 \text{ V}$	$V_{DS} = 100 \text{ V}$, $T_J = 125^\circ\text{C}$	-	-	50		
		$V_{GS} = 0 \text{ V}$	$V_{DS} = 100 \text{ V}$, $T_J = 175^\circ\text{C}$	-	-	150		
On-state drain current ^a	$I_{D(\text{on})}$	$V_{GS} = 10 \text{ V}$	$V_{DS} \geq 5 \text{ V}$	40	-	-	A	
Drain-source on-state resistance ^a	$R_{DS(\text{on})}$	$V_{GS} = 10 \text{ V}$	$I_D = 10 \text{ A}$	-	0.0072	0.0086	Ω	
		$V_{GS} = 4.5 \text{ V}$	$I_D = 10 \text{ A}$	-	0.0095	0.0114		
		$V_{GS} = 10 \text{ V}$	$I_D = 5 \text{ A}$, $T_J = 125^\circ\text{C}$	-	-	0.0110		
		$V_{GS} = 10 \text{ V}$	$I_D = 5 \text{ A}$, $T_J = 175^\circ\text{C}$	-	-	0.0187		
Forward Transconductance ^b	g_{fs}	$V_{DS} = 15 \text{ V}$, $I_D = 10 \text{ A}$		-	52	-	S	
Dynamic ^b								
Input capacitance	C_{iss}	$V_{GS} = 0 \text{ V}$	$V_{DS} = 50 \text{ V}$, $f = 1 \text{ MHz}$	-	2266	2832	pF	
Output capacitance	C_{oss}			-	799	1000		
Reverse transfer capacitance	C_{rss}			-	34	43		
Total gate charge ^c	Q_g	$V_{GS} = 10 \text{ V}$	$V_{DS} = 50 \text{ V}$, $I_D = 10 \text{ A}$	-	46	58	nC	
Gate-source charge ^c	Q_{gs}			-	7	-		
Gate-drain charge ^c	Q_{gd}			-	10	-		
Gate resistance	R_g	$f = 1 \text{ MHz}$		1.1	1.9	3.0	Ω	
Turn-on delay time ^c	$t_{d(\text{on})}$	$V_{DD} = 40 \text{ V}$, $R_L = 4 \Omega$ $I_D \geq 10 \text{ A}$, $V_{GEN} = 10 \text{ V}$, $R_g = 1 \Omega$		-	11	14	ns	
Rise time ^c	t_r			-	4	5		
Turn-off delay time ^c	$t_{d(\text{off})}$			-	33	42		
Fall time ^c	t_f			-	7	8		
Source-Drain Diode Ratings and Characteristics ^b								
Pulsed current ^a	I_{SM}			-	-	280	A	
Forward voltage	V_{SD}	$I_F = 40 \text{ A}$, $V_{GS} = 0$		-	1	1.2	V	

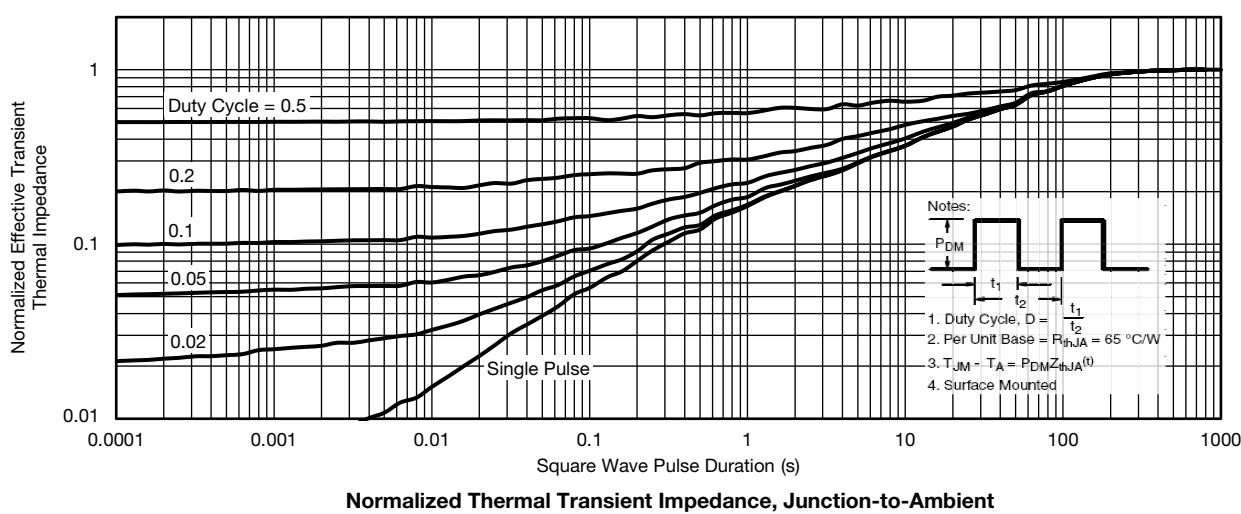
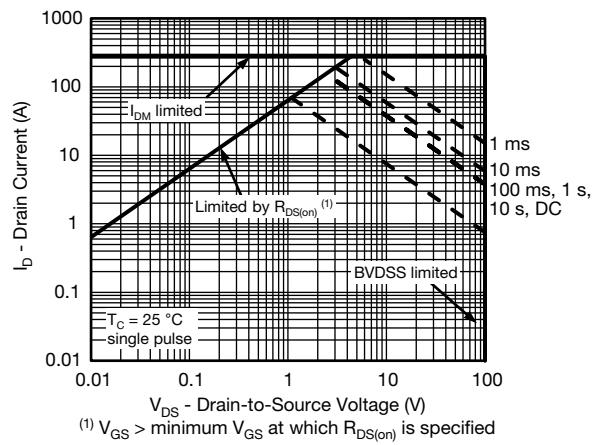
Notes

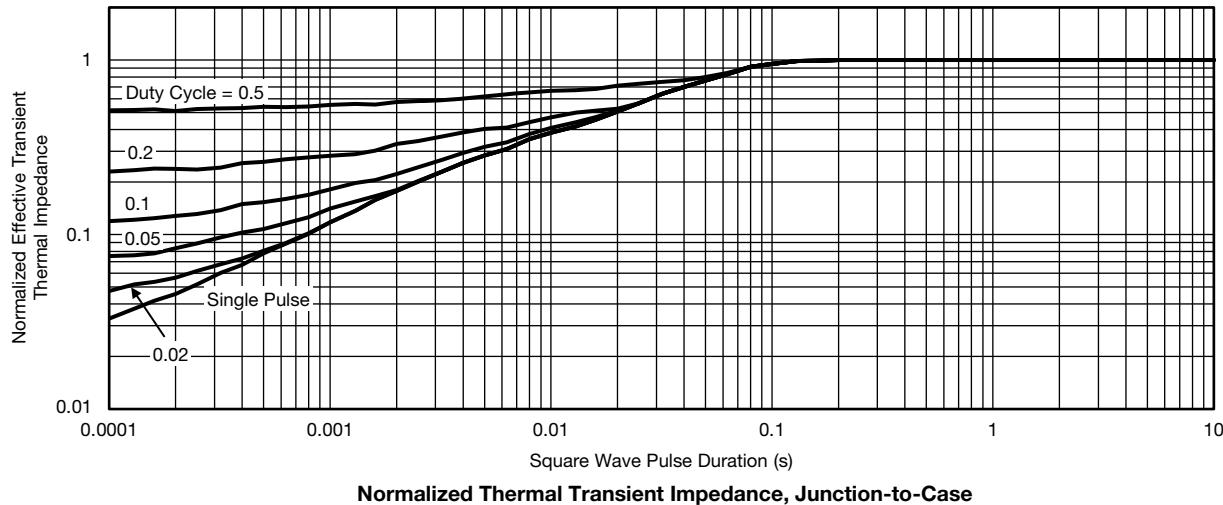
- a. Pulse test; pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, unless otherwise noted)


TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, unless otherwise noted)

Capacitance

Source Drain Diode Forward Voltage

On-Resistance vs. Junction Temperature

Threshold Voltage

On-Resistance vs. Gate-to-Source Voltage

Drain Source Breakdown vs. Junction Temperature

THERMAL RATINGS ($T_A = 25^\circ\text{C}$, unless otherwise noted)


THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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